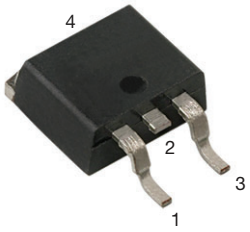
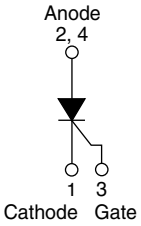
Thyristor Surface Mount, Phase Control SCR, 16 A



D²PAK (TO-263AB)



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS16SLHM3 of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications.

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	16 A
V_{DRM}/V_{RRM}	1600 V
V_{TM}	1.25 V
I_{GT}	45 mA
T_J	-40 °C to +125 °C
Package	D²PAK (TO-263AB)
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 µm) copper	3.5	5.5	A
Aluminum IMS, R_{thCA} = 15 °C/W	8.5	13.5	
Aluminum IMS with heatsink, R_{thCA} = 5 °C/W	16.5	25.0	

Note

- T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
I_{RMS}		25	
V_{RRM}/V_{DRM}		1600	V
I_{TSM}		350	A
V_T	16 A, T_J = 25 °C	1.25	V
dV/dt		500	V/µs
dI/dt		150	A/µs
T_J		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM}, MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM}, MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM}, AT 125 °C mA
VS-25TTS16SLHM3	1600	1600	10

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES TYP.	VALUES MAX.	UNITS
Maximum average on-state current	$I_{T(AV)}$	T_C = 93 °C, 180° conduction half sine wave	16		A
Maximum RMS on-state current	I_{RMS}		25		A
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	300		A
		10 ms sine pulse, no voltage reapplied	350		A
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	450		A^2s
		10 ms sine pulse, no voltage reapplied	630		A^2s
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied	6300		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	16 A, T_J = 25 °C	1.25		V
On-state slope resistance	r_t	T_J = 125 °C	12.0		mΩ
Threshold voltage	$V_{T(TO)}$	T_J = 125 °C	1.0		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T_J = 25 °C, V_R = Rated V_{RRM}/V_{DRM}	0.5		mA
		T_J = 125 °C, V_R = Rated V_{RRM}/V_{DRM}	10		mA
Holding current	I_H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	-	150	mA
Maximum latching current	I_L	Anode supply = 6 V, resistive load, T_J = 25 °C	200		mA
Maximum rate of rise of off-state voltage	dV/dt	T_J = T_J max., linear to 80 %, V_{DRM} = R_g - k = Open	500		V/µs
Maximum rate of rise of turned-on current	dI/dt		150		A/µs

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	W
Maximum peak positive gate current	+ I_{GM}		1.5	A
Maximum peak negative gate voltage	- V_{GM}		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	60	mA
		Anode supply = 6 V, resistive load, T_J = 25 °C	45	mA
		Anode supply = 6 V, resistive load, T_J = 125 °C	20	mA
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	2.5	V
		Anode supply = 6 V, resistive load, T_J = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}	T_J = 125 °C, V_{DRM} = Rated value	0.25	
Maximum DC gate current not to trigger	I_{GD}		2.0	mA

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	T_J = 25 °C	0.9	µs
Typical reverse recovery time	t_{rr}	T_J = 125 °C	4	µs
Typical turn-off time	t_q	T_J = 125 °C	110	µs

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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	260	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.1	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	R_{thJA} (1)		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D^2PAK (TO-263AB)	25TTS16SH	

Note

(1) When mounted on 1" square (650 mm^2) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

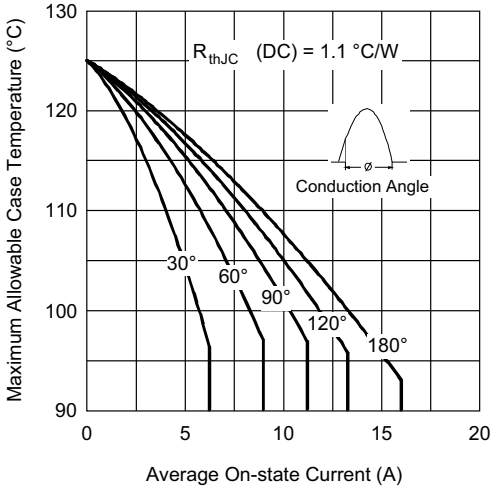


Fig. 1 - Current Rating Characteristics

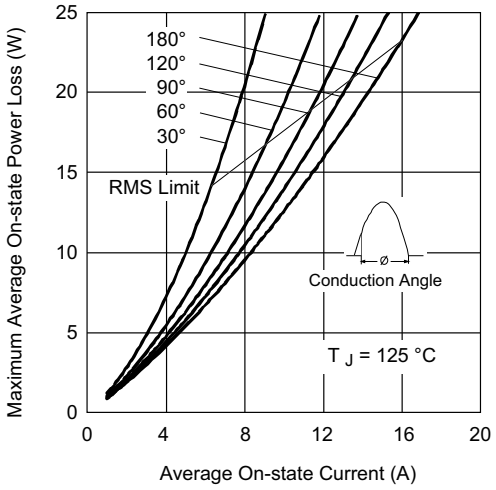


Fig. 3 - On-State Power Loss Characteristics

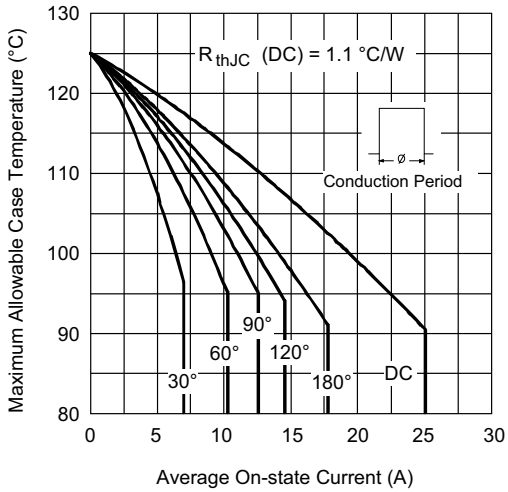


Fig. 2 - Current Rating Characteristics

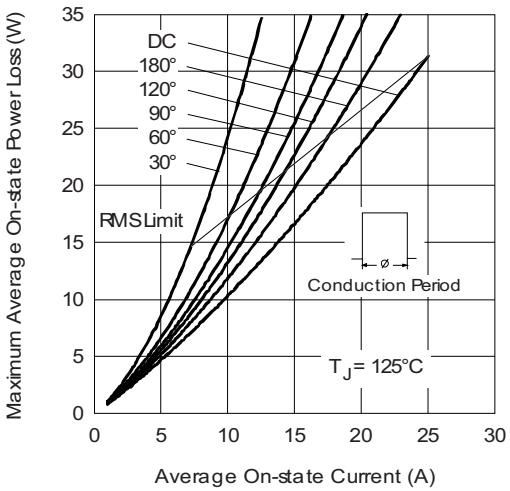


Fig. 4 - On-State Power Loss Characteristics

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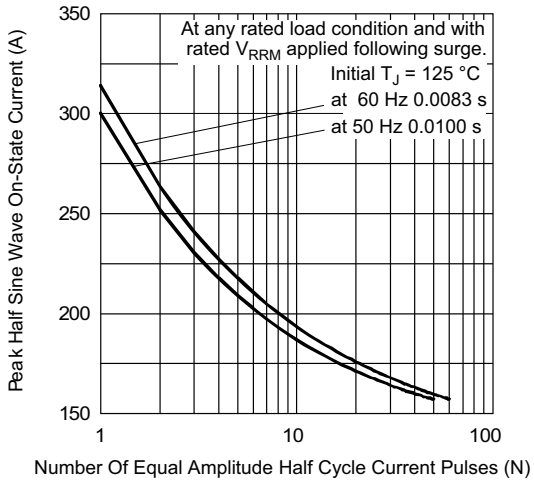


Fig. 5 - Maximum Non-Repetitive Surge Current

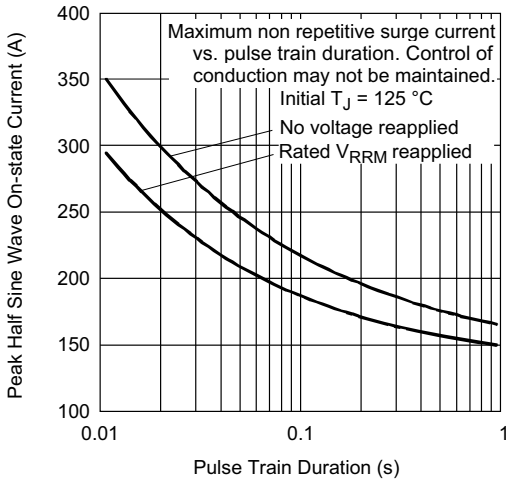


Fig. 6 - Maximum Non-Repetitive Surge Current

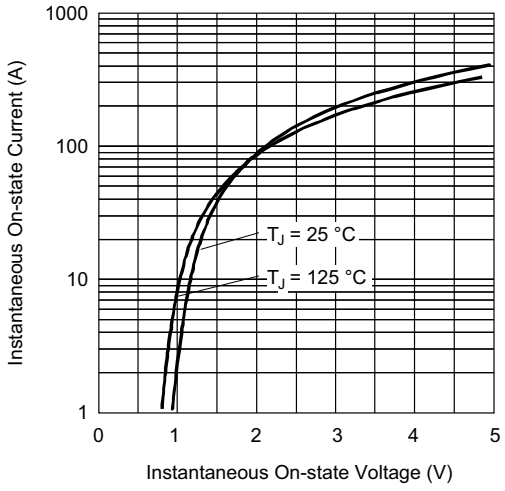


Fig. 7 - On-State Voltage Drop Characteristics

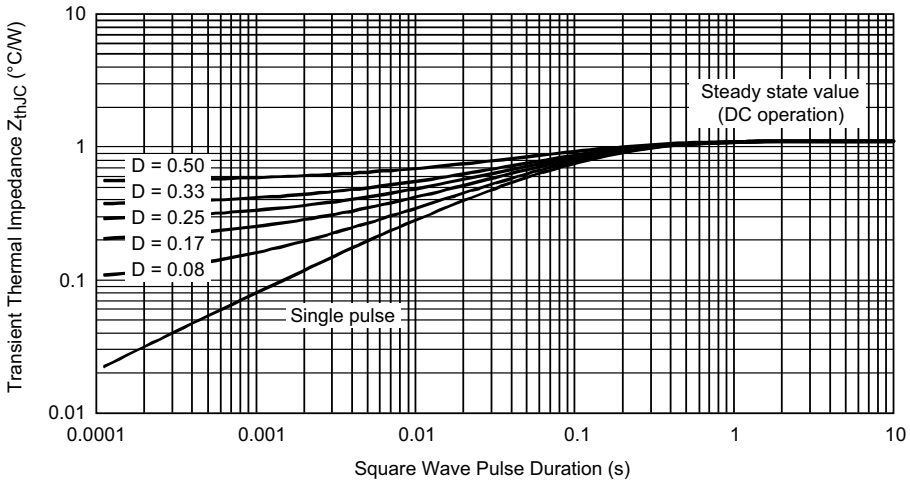


Fig. 8 - Gate Characteristics

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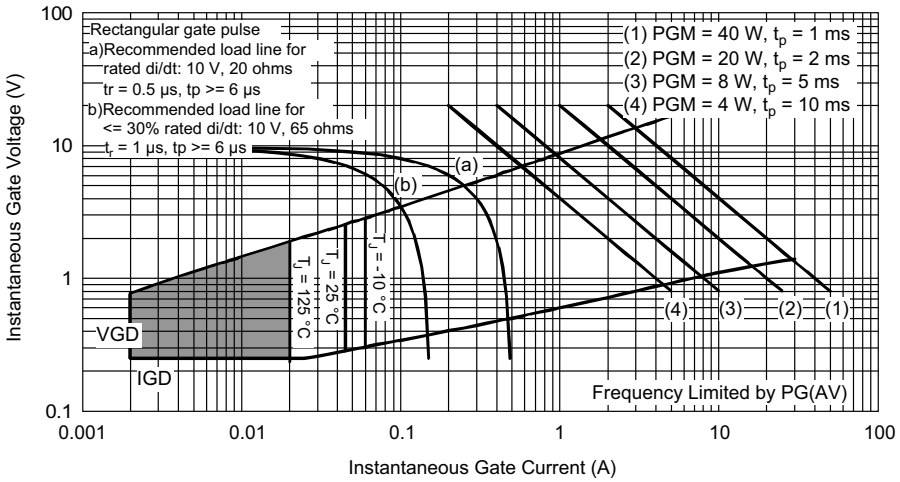


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code

VS-	25	T	T	S	16	S	L	H	M3
1	2	3	4	5	6	7	8	9	10

1 - Vishay Semiconductors product

2 - Current rating (25 = 25 A)

3 - Circuit configuration:
T = single thyristor

4 - Package:
T = D^2PAK (TO-263AB)

5 - Type of silicon:
S = standard recovery rectifier

6 - Voltage rating: Voltage code x 100 = V_{RRM} — 16 = 1600 V

7 - S = surface mountable

8 - L = tape and reel (left oriented), for different orientation, contact factory

9 - H = AEC-Q101 qualified

10 - Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

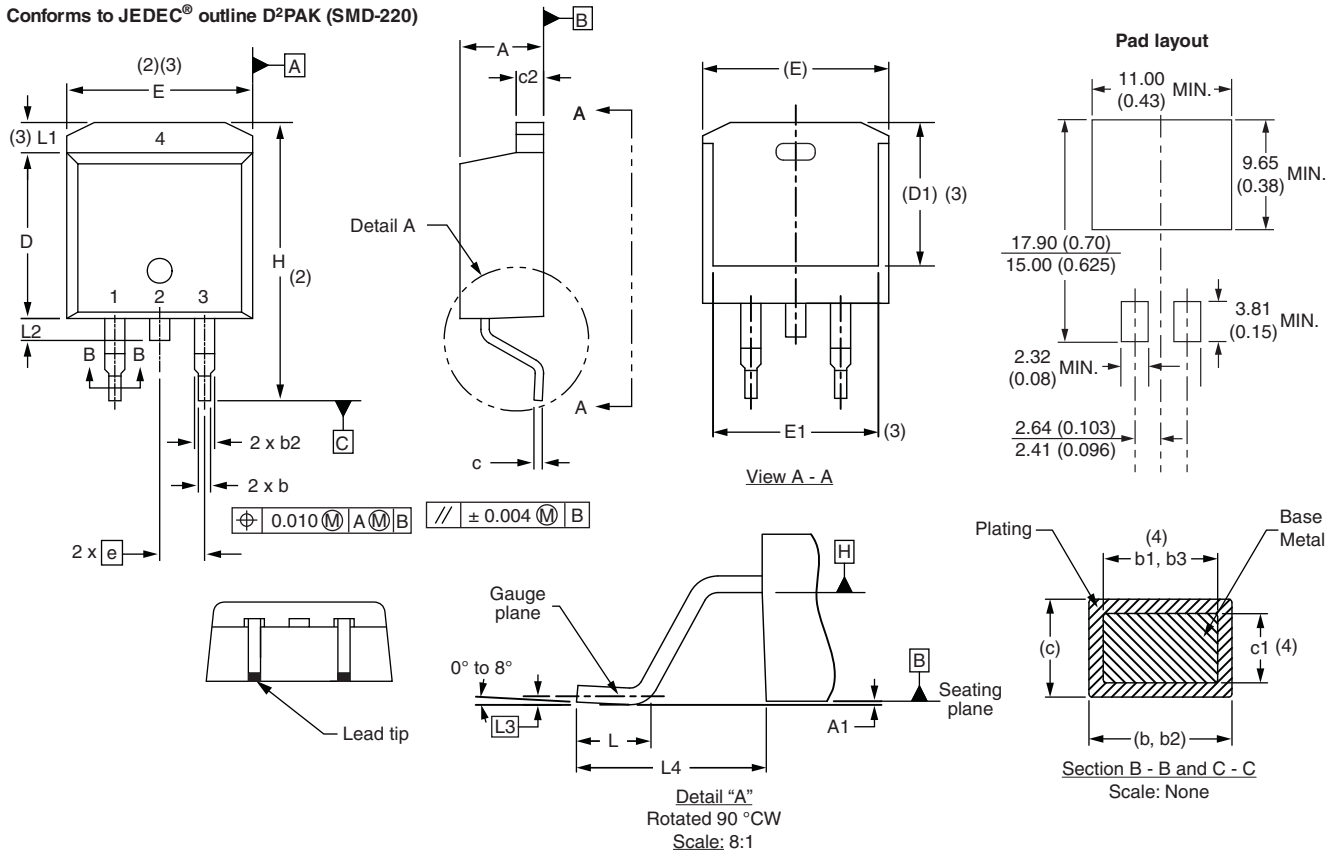
ORDERING INFORMATION (Example)			
PREFERRED P/N	**QUANTITY PER T/R**	**MINIMUM ORDER QUANTITY**	**PACKAGING DESCRIPTION**
VS-25TTS16SLHM3	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95444
Packaging information	www.vishay.com/doc?96317

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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

(1) Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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